



THE DATASHEET OF ZTX457STZ



NPN SILICON PLANAR ME HIGH VOLTAGE TRANSIS

ISSUE 2 – MARCH 1994

FEATURES

- * 300 Volt V_{CEO}
- * 0.5 Amp continuous current
- * $P_{tot} = 1$ Watt

ABSOLUTE MAXIMUM RATINGS

PARAMETER	
Collector-Base Voltage	
Collector-Emitter Voltage	
Emitter-Base Voltage	
Peak Pulse Current	
Continuous Collector Current	
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	
Operating and Storage Temperature	

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	MIN
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	30
Collector-Emitter Breakdown Voltage	$V_{CEO(sus)}$	30
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5
Collector Cut-Off Current	I_{CBO}	
Emitter Cut-Off Current	I_{EBO}	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	
Base-Emitter Turn On Voltage	$V_{BE(on)}$	
Static Forward Current Transfer Ratio	h_{FE}	50 50 25
Transition Frequency	f_T	75

*Measured under pulsed conditions. Pulses

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